каталог, описание, технические, характеристики, datasheet, параметры, маркировка,габариты, фото,
модуль, Infineon, Eupec

КАТАЛОГ

модуль , igbt,

модуль igbt Infineon FS450R12KE3_S1, FS450R12KE3

купить, продажа

электронные компоненты

Мы не работаем с частными (физическими) лицами.Мы работаем только с юридическими лицами(организациями) и ИП и только по безналичному расчёту.

где и как купить в Минске?

fs450r17ke3bosa1	infineon, trans igbt n-ch 1700v 605a 2250000mw 29-pin econopp-1 tray
fs450r17ke4	infineon, transistor polarity:n channel; dc collector current:450a; collector emitter voltage vces:1.7kv; power dissipation pd:2.5kw;
collector emitter voltage v(br)ceo:1.7kv;	
eb01-fs450r12ke3	power integrations
eb01-fs450r12ke4	power integrations
eb01-fs450r17ke3	power integrations
fs450r12ke3	infineon technologies
fs450r12ke4	infineon technologies
fs450r12oe4	infineon technologies
fs450r12oe4p	infineon technologies

fs450r17ke3 infineon technologies, igbt s 1700v 450a 3-phase

fs450r17ke4 infineon technologies

fs450r17oe4 infineon technologies

fs450r17oe4p infineon technologies, igbt s

fs450r12ke3bosa1 infineon technologies

fs450r12ke4bosa1 infineon technologies

fs450r12oe4bosa1 infineon technologies

fs450r12oe4pbosa1 infineon technologies

fs450r17ke3 infineon technologies

fs450r17ke3bosa1 infineon technologies

fs450r17ke4bosa1 infineon technologies

fs450r17oe4bosa1 infineon technologies

fs450r17oe4pbosa1 infineon technologies

fs450r12ke3 eupec igbt модуль 450a 1200v

fs450r12ke3-s1 eupec igbt модуль 50a 1200v

fs450r12ke3 infineon, igbt s 1200v 450a 3-phase.

fs450r12ke3 infineon technologies industrial power and controls americas, igbt 1200v 450a.

fs450r12ke3bosa1 infineon technologies, igbt 1200v 450a.

fs450r12ke3bosa1 infineon, ag-econopp-1.

fs450r12oe4 infineon, igbt s igbt 450a 1200v.

fs450r12oe4 infineon technologies industrial power and controls americas, igbt 1200v 450a.

fs450r12oe4bosa1 infineon technologies, igbt 1200v 450a.

fs450r17ke3bosa1 infineon, / м.опт: 501-9999 шт. опт: от 10000 шт.

fs450r12ke3 infineon

fs450r12oe4 infineon

fs450r12ke3

fs450r12ke3bosa1

fs450r12ke4bosa1

fs450r12oe4

fs450r12oe4bosa1

fs450r12oe4pbosa1

fs450r17ke3bosa1

fs450r17ke4bosa1

fs450r17oe4bosa1

fs450r17oe4pbosa1

fs450r12ke3bosa1 /infineon/

fs450r12ke4bosa1 /infineon/

fs450r12ke4bosa1 /infineon/ moq>4 infineon

fs450r12oe4 /infineon/ moq>4 infineon

fs450r12oe4bosa1 /infineon/ moq> 1 infineon

fs450r12oe4bosa1 /infineon/

fs450r12oe4pbosa1 /infineon/ moq> 5 infineon

fs450r12oe4pbosa1 /infineon/

fs450r17ke3bosa1 /infineon/

fs450r17ke4bosa1 /infineon/

fs450r17oe4bosa1 /infineon/

fs450r17oe4pbosa1 /infineon/

fs450r12oe4 inf, оптовая цена от 4 шт.

fs450r12ke3bosa1 infin, 2-5 дней на заказ ag-econopp-1

fs450r12ke3bosa1 infineon technologies ag (siemens semiconductors), igbt s up to 1200v, econopack + b-series 1200v sixpack igbt with trench/fieldstop igbt3 and emitter controlled he diode воз…

fs450r12ke4bosa1 infineon technologies ag (siemens semiconductors), sixpack

fs450r12oe4 infineon technologies ag (siemens semiconductors), igbt s igbt 450a 1200v

fs450r12oe4bosa1 infineon technologies ag (siemens semiconductors), igbt s up to 1200v, econopack + d-series 1200v sixpack igbt with trench/fieldstop igbt4, emitter controlled he diode, ntc and pressf…

fs450r12oe4pbosa1 infineon technologies ag (siemens semiconductors), sixpack

fs450r17ke3bosa1 infineon technologies ag (siemens semiconductors), igbt s up to 1600v / 1700v, econopack + b-series 1700v sixpack igbt with trench/fieldstop igbt3 and emitter controlled 3 diode воз…

fs450r17ke4bosa1 infineon technologies ag (siemens semiconductors)

fs450r17oe4bosa1 infineon technologies ag (siemens semiconductors), igbt s up to 1600v / 1700v, econopack + d-series 1700v sixpack igbt with trench/fieldstop igbt4, emitter controlled he diode, ntc and pressf…

fs450r17oe4pbosa1 infineon technologies ag (siemens semiconductors)

fs450r12ke3bosa1

fs450r12oe4

fs450r12oe4bosa1

fs450r12oe4pbosa1

eb01-fs450r12ke3 power integrations, gate dvr p&p scale 1

eb01-fs450r12ke3 power integrations, средства разработки интегральных схем (ис) управления питанием eb01

eb01-fs450r12ke4 power integrations, средства разработки интегральных схем (ис) управления питанием eb01

eb01-fs450r12ke4 power integrations, gate dvr p&p scale 1

eb01-fs450r17ke3 power integrations, gate dvr p&p scale 1

eb01-fs450r17ke3 power integrations, средства разработки интегральных схем (ис) управления питанием eb01

fs450r12ke3 infineon technologies, модули биполярных транзисторов с изолированным затвором (igbt) 1200v 450a 3-phase

fs450r12ke3 infineon technologies, транзисторы импортные

fs450r12ke3bosa1 infin

fs450r12ke3bosa1 infineon technologies, igbt 1200v 450a

fs450r12ke3bosa1 infin, igbt б гм

fs450r12ke3bosa1 infineon technologies, ag-econopp 1/igbt s to 1600v/1700v

fs450r12ke4 infineon technologies, модули биполярных транзисторов с изолированным затвором (igbt) 1200v 450a igbt4

fs450r12ke4bdsa1 rochester electronics, igbt 1200v 450a

fs450r12ke4bosa1 infineon technologies, mod igbt med pwr econopp-1

fs450r12oe4 infineon technologies, модули биполярных транзисторов с изолированным затвором (igbt) igbt 450a 1200v

fs450r12oe4 infineon technologies, infineon fs450r12oe4 nйй igbt же, 3 з, 450 a 1200 v, 29й econopack+еи

fs450r12oe4 infineon technologies, igbt4 trench/field

fs450r12oe4bosa1 infineon technologies, with trench/fieldstop igbt4 and emitter controlled he diode and pres

fs450r12oe4bosa1 infineon technologies, igbt 1200v 450a

fs450r12oe4bosa1 infineon technologies, igbt , medium power econo

fs450r12oe4bosa1 infin

fs450r12oe4bosa1 infineon technologies, trans igbt n-ch 1.2kv 660a 29-pin tray

fs450r12oe4p infineon technologies, модули биполярных транзисторов с изолированным затвором (igbt)

fs450r12oe4pbosa1 infineon technologies, igbt, , n-ch, 1.2kv, 450a

fs450r12oe4pbosa1 infin

fs450r12oe4pbosa1 infineon technologies, mod igbt med pwr econopp-2

fs450r17ke3 infineon technologies, модули биполярных транзисторов с изолированным затвором (igbt) 1700v 450a 3-phase

fs450r17ke3 infineon technologies, 1

fs450r17ke3bosa1 infineon technologies, ag-econopp 1/igbt s to 1600v/1700v

fs450r17ke3bosa1 infineon technologies, mod igbt med pwr econopp-1

fs450r17ke3bosa1 infineon technologies, 2

fs450r17ke4 infineon technologies, модули биполярных транзисторов с изолированным затвором (igbt) igbt 1700v 450a

fs450r17ke4bosa1 infineon technologies, mod igbt med pwr econopp-1

fs450r17ke4bosa1 infineon technologies, medium power econo

fs450r17oe4 infineon technologies, модули биполярных транзисторов с изолированным затвором (igbt) igbt 450a 1700v

fs450r17oe4bosa1 infineon technologies, mod igbt med pwr econopp-2

fs450r17oe4p infineon technologies, модули биполярных транзисторов с изолированным затвором (igbt)

fs450r17oe4pbosa1 infineon technologies, medium power econo

fs450r17oe4pbosa1 infineon technologies, mod igbt med pwr econopp-2

mtsw-108-10-f-s-450-ra samtec, modified .025 square post termin

fs450r12ke3bosa1 infin, ag-econopp-1

fs450r12ke3

fs450r12ke3-s1

fs450r12ke4

fs450r17ke3

fs450r17ke3/agdr-71c

fs450r17ke4

fs450r12ke3 eupec, eupec igbt 450a 1200v

fs450r12ke3-s1 eupec, eupec igbt 50a 1200v

fs450r12oe4 infineon, igbt4 trench/field

fs450r17ke3 unknown

fs450r17ke3 inf, igbt-модуль, 1700в, 450а

fs450r17ke4 unknown

fs450r17ke4 inf

fs450r12ke3bosa1 infin, igbt силовой модуль

fs450r12kt3

eb01-fs450r12ke3 power integrations, gate dvr p&p scale 1

eb01-fs450r12ke4 power integrations, gate dvr p&p scale 1

eb01-fs450r17ke3 power integrations, gate dvr p&p scale 1

mtsw-108-10-f-s-450-ra samtec inc., modified .025 square post termin

fs450r12k infineon technologies

fs450r12o infineon technologies

fs450r17k infineon technologies

fs450r12ke3 infineon, модули биполярных транзисторов с изолированным затвором (igbt) 1200v 450a 3-phase

fs450r12ke3-s1 eupec

fs450r12ke3_b7eng eupec,

fs450r12ke3_s1 infineon technologies

fs450r12ke4 infineon, дискретные полупроводниковые модули 1200v 450a igbt4

fs450r12kt3 mitsubishi

fs450r12kt4 infineon

fs450r17ke3 infineon, модули биполярных транзисторов с изолированным затвором (igbt) 1700v 450a 3-phase

fs450r17ke3_s1 eupec infineon, there are no reviews yet.

fs450r17ke4 infineon, модули биполярных транзисторов с изолированным затвором (igbt) igbt 1700v 450a

fs450r12ke3 bosa1, транзисторный модуль

fs450r12ke3, транзисторный модуль

fs450r12ke3-s1 транзисторный модуль

fs450r12ke3 eupec [eupec gmbh], модули биполярных транзисторов с изолированным затвором (igbt) 1200v 450a 3-phase

fs450r12ke3-s1 eupec infineon, fs450r12ke3-s1, igbt-s; igbt standard/power s; 50 amp; 1200 volt

fs450r12ke4 infineon [infineon technologies ag], модули биполярных транзисторов с изолированным затвором (igbt) 1200v 450a igbt4

fs450r12kt3 infineon

fs450r17ke3 eupec [eupec gmbh], модули биполярных транзисторов с изолированным затвором (igbt) 1700v 450a 3-phase

fs450r17ke4 infineon [infineon technologies ag], модули биполярных транзисторов с изолированным затвором (igbt) igbt 1700v 450a

fs450r12ke3-s1 infineon technologies

fs450r12ke3bosa1 infineon technologies, econopack + b-series 1200v sixpack igbt with trench/fieldstop igbt3 and emitter controlled he diode | summary ...

fs450r12oe4bosa1 infineon technologies, econopack + d-series 1200v sixpack igbt with trench/fieldstop igbt4, emitter controlled he diode, ntc and pres...

fs450r17ke3bosa1 infineon technologies, trans igbt n-ch 1700v 605a 2250000mw 29-pin tray

fs450r120e4p infineon, igbts

fs450r12oe4p infineon [infineon technologies ag], модули биполярных транзисторов с изолированным затвором (igbt)

fs450r17oe4bosa1 infineon, igbts

fs450r17oe4p infineon [infineon technologies ag], модули биполярных транзисторов с изолированным затвором (igbt)

Technische Information / Technical Information

IGBT-Module
IGBT-modules

FS450R12KE3

- EconoPACK™+ Modul mit Trench/Feldstop IGBT3 und High Efficiency Diode
- EconoPACK™+ with trench/fieldstop IGBT3 and Emitter Controlled High Efficiency diode

IGBT,Wechselrichter / IGBT,Inverter

Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	T_{vj} = 25°C	V_{CES}	1200	V
Kollektor-Dauergleichstrom Continuous DC collector current	T_C = 80°C, $T_{vj\,max}$ = 150°C T_C = 25°C, $T_{vj\,max}$ = 150°C	$I_{C\,nom}$ I_C	450 600	A A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	t_P = 1 ms	I_{CRM}	900	A
Gesamt-Verlustleistung Total power dissipation	T_C = 25°C, $T_{vj\,max}$ = 150	P_{tot}	2100	W
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	I_C = 450 A, V_{GE} = 15 V I_C = 450 A, V_{GE} = 15 V	T_{vj} = 25°C T_{vj} = 125°C	$V_{CE\,sat}$		1,70 2,00	2,15	V V
Gate-Schwellenspannung Gate threshold voltage	I_C = 18,0 mA, V_{CE} = V_{GE}, T_{vj} = 25°C		V_{GEth}	5,0	5,8	6,5	V
Gateladung Gate charge	V_{GE} = -15 V ... +15 V		Q_G		4,30		µC
Interner Gatewiderstand Internal gate resistor	T_{vj} = 25°C		R_{Gint}		1,7		Ω
Eingangskapazität Input capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{ies}		32,0		nF
Rückwirkungskapazität Reverse transfer capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{res}		1,50		nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	V_{CE} = 1200 V, V_{GE} = 0 V, T_{vj} = 25°C		I_{CES}			5,0	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25°C		I_{GES}			400	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	I_C = 450 A, V_{CE} = 600 V V_{GE} = ±15 V R_{Gon} = 1,6 Ω	T_{vj} = 25°C T_{vj} = 125°C	$t_{d\,on}$		0,25 0,30		µs µs
Anstiegszeit, induktive Last Rise time, inductive load	I_C = 450 A, V_{CE} = 600 V V_{GE} = ±15 V R_{Gon} = 1,6 Ω	T_{vj} = 25°C T_{vj} = 125°C	t_r		0,09 0,10		µs µs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	I_C = 450 A, V_{CE} = 600 V V_{GE} = ±15 V R_{Goff} = 1,6 Ω	T_{vj} = 25°C T_{vj} = 125°C	$t_{d\,off}$		0,55 0,65		µs µs
Fallzeit, induktive Last Fall time, inductive load	I_C = 450 A, V_{CE} = 600 V V_{GE} = ±15 V R_{Goff} = 1,6 Ω	T_{vj} = 25°C T_{vj} = 125°C	t_f		0,13 0,16		µs µs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	I_C = 450 A, V_{CE} = 600 V, L_S = 80 nH V_{GE} = ±15 V R_{Gon} = 1,6 Ω	T_{vj} = 25°C T_{vj} = 125°C	E_{on}		33,0		mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	I_C = 450 A, V_{CE} = 600 V, L_S = 80 nH V_{GE} = ±15 V R_{Goff} = 1,6 Ω	T_{vj} = 25°C T_{vj} = 125°C	E_{off}		65,0		mJ mJ
Kurzschlußverhalten SC data	V_{GE} ≤ 15 V, V_{CC} = 900 V V_{CEmax} = V_{CES} -L_{sCE} ·di/dt	t_P ≤ 10 µs, T_{vj} = 125°C	I_{SC}		1800		A
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro IGBT / per IGBT		R_{thJC}			0,06	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro IGBT / per IGBT λ_{Paste} = 1 W/(m·K) / λ_{grease} = 1 W/(m·K)		R_{thCH}		0,048		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\,op}$	-40		125	°C

prepared by: MB	date of publication: 2013-10-02
approved by: WR	revision: 3.1

Diode, Wechselrichter / Diode, Inverter

Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}	1200	V
Dauergleichstrom Continuous DC forward current		I_F	450	A
Periodischer Spitzenstrom Repetitive peak forward current	t_P = 1 ms	I_{FRM}	900	A
Grenzlastintegral I²t - value	V_R = 0 V, t_P = 10 ms, T_{vj} = 125°C	I²t	35000	A²s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	I_F = 450 A, V_{GE} = 0 V I_F = 450 A, V_{GE} = 0 V	T_{vj} = 25°C T_{vj} = 125°C	V_F		1,65 1,65	2,15	V V
Rückstromspitze Peak reverse recovery current	I_F = 450 A, - di_F/dt = 5200 A/µs (T_{vj}=125°C) V_R = 600 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C	I_{RM}		315 405		A A
Sperrverzögerungsladung Recovered charge	I_F = 450 A, - di_F/dt = 5200 A/µs (T_{vj}=125°C) V_R = 600 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C	Q_r		45,0 85,0		µC µC
Abschaltenergie pro Puls Reverse recovery energy	I_F = 450 A, - di_F/dt = 5200 A/µs (T_{vj}=125°C) V_R = 600 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C	E_{rec}		21,0 39,0		mJ mJ
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro Diode / per diode		R_{thJC}			0,10	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Diode / per diode λ_{Paste} = 1 W/(m·K) / λ_{grease} = 1 W/(m·K)		R_{thCH}		0,08		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\,op}$	-40		125	°C

NTC-Widerstand / NTC-Thermistor

Charakteristische Werte / Characteristic Values

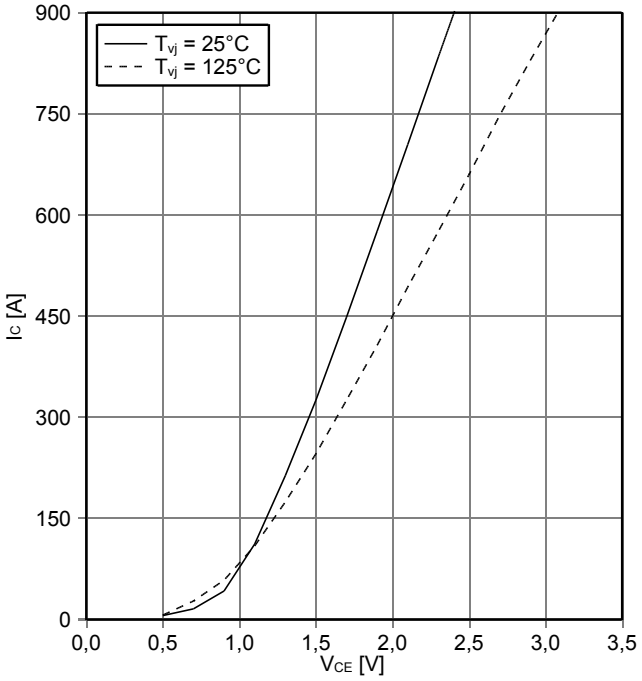
			min.	typ.	max.	
Nennwiderstand Rated resistance	T_C = 25°C	R_{25}		5,00		kΩ
Abweichung von R100 Deviation of R100	T_C = 100°C, R_{100} = 493 Ω	ΔR/R	-5		5	%
Verlustleistung Power dissipation	T_C = 25°C	P_{25}			20,0	mW
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298{,}15\ K))]$	$B_{25/50}$		3375		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298{,}15\ K))]$	$B_{25/80}$		t.b.d.		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298{,}15\ K))]$	$B_{25/100}$		t.b.d.		K

Angaben gemäß gültiger Application Note.
Specification according to the valid application note.

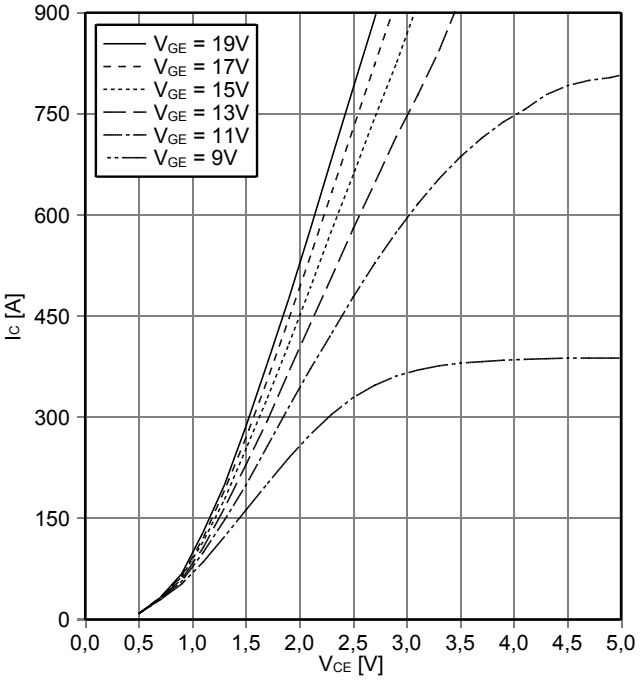
Modul / Module

Isolations-Prüfspannung Isolation test voltage	RMS, f = 50 Hz, t = 1 min	V_{ISOL}		2,5		kV
Innere Isolation Internal isolation	Basisisolierung (Schutzklasse 1, EN61140) basic insulation (class 1, IEC 61140)			Al_2O_3		
Kriechstrecke Creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal			14,5		mm
Luftstrecke Clearance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal			10,0		mm
Vergleichszahl der Kriechwegbildung Comperative tracking index		CTI		> 225		
			min.	typ.	max.	
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Modul / per module λ_{Paste} = 1 W/(m·K) / λ_{grease} = 1 W/(m·K)	R_{thCH}		0,005		K/W
Modulstreuinduktivität Stray inductance module		L_{sCE}		20		nH
Modulleitungswiderstand, Anschlüsse - Chip Module lead resistance, terminals - chip	T_C = 25°C, pro Schalter / per switch	$R_{CC'+EE'}$		1,10		mΩ
Lagertemperatur Storage temperature		T_{stg}	-40		125	°C
Anzugsdrehmoment f. Modulmontage Mounting torque for modul mounting	Schraube M5 - Montage gem. gültiger Applikationsschrift Screw M5 - Mounting according to valid application note	M	3,00	-	6,00	Nm
Anzugsdrehmoment f. elektr. Anschlüsse Terminal connection torque	Schraube M6 - Montage gem. gültiger Applikationsschrift Screw M6 - Mounting according to valid application note	M	3,0	-	6,0	Nm
Gewicht Weight		G		910		g

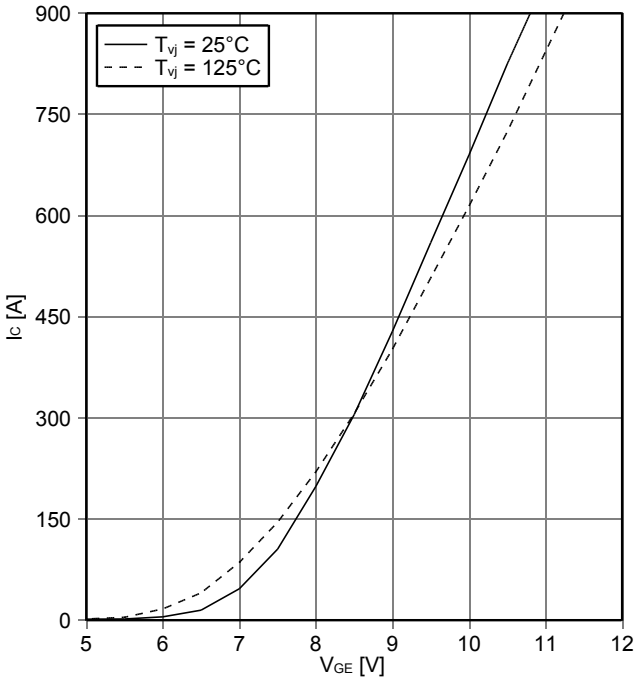
Ausgangskennlinie IGBT,Wechselrichter (typisch)
output characteristic IGBT,Inverter (typical)
$I_C = f(V_{CE})$
V_{GE} = 15 V



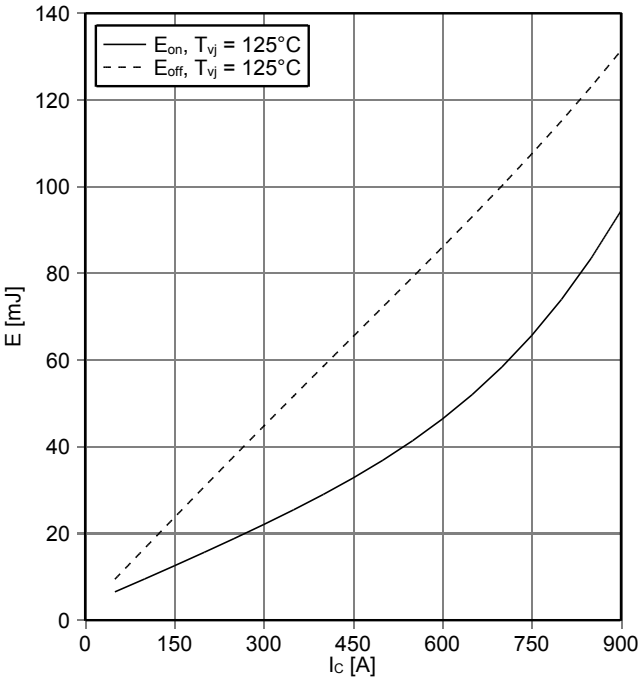
Ausgangskennlinienfeld IGBT,Wechselrichter (typisch)
output characteristic IGBT,Inverter (typical)
$I_C = f(V_{CE})$
T_{vj} = 125°C



Übertragungscharakteristik IGBT,Wechselrichter (typisch)
transfer characteristic IGBT,Inverter(typical)
$I_C = f(V_{GE})$
V_{CE} = 20 V



SchaltverlusteIGBT,Wechselrichter (typisch)
switching losses IGBT,Inverter (typical)
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
V_{GE} = ±15 V, R_{Gon} = 1.6 Ω, R_{Goff} = 1.6 Ω, V_{CE} = 600 V



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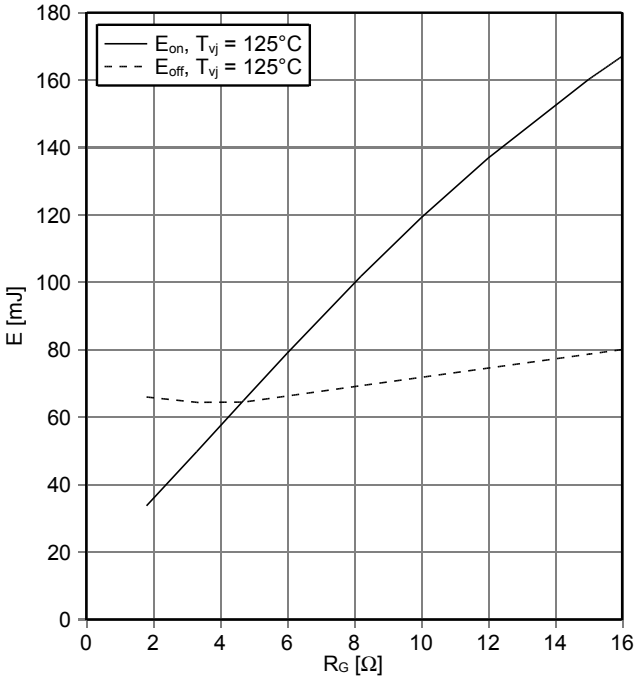
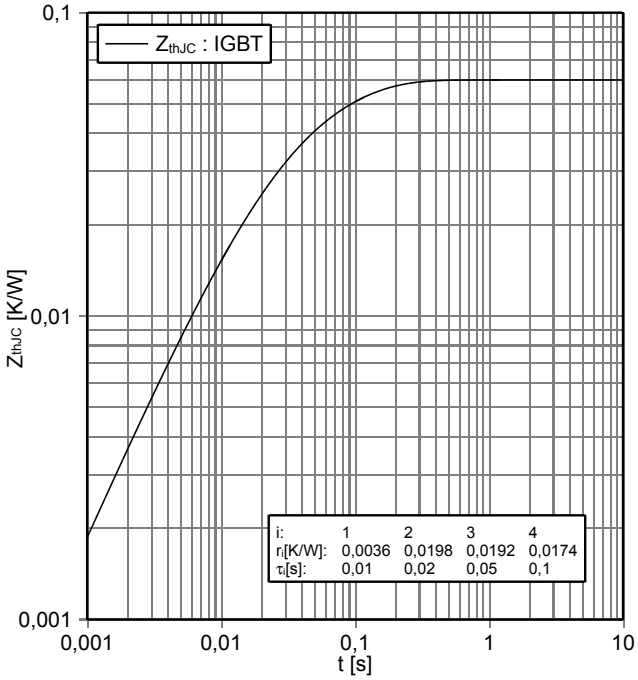
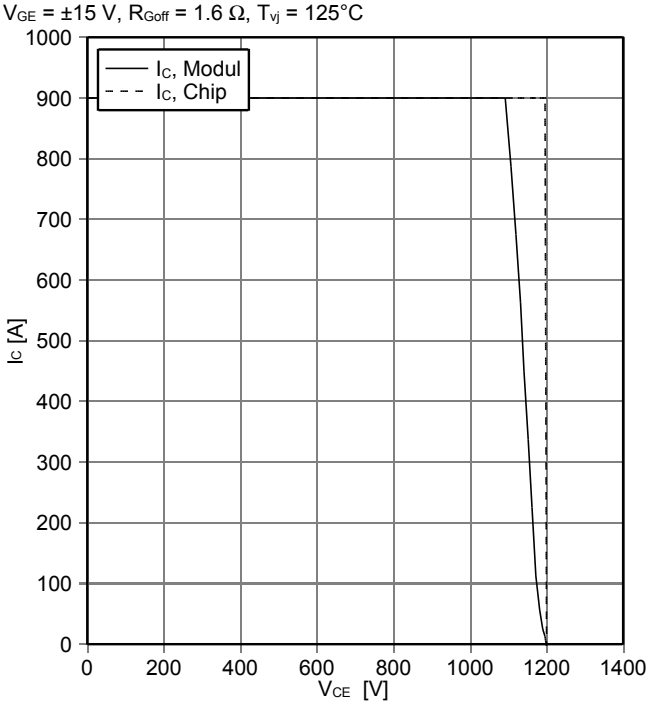
SchaltverlusteIGBT,Wechselrichter (typisch)
switching losses IGBT,Inverter (typical)
$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
V_{GE} = ±15 V, I_C = 450 A, V_{CE} = 600 V



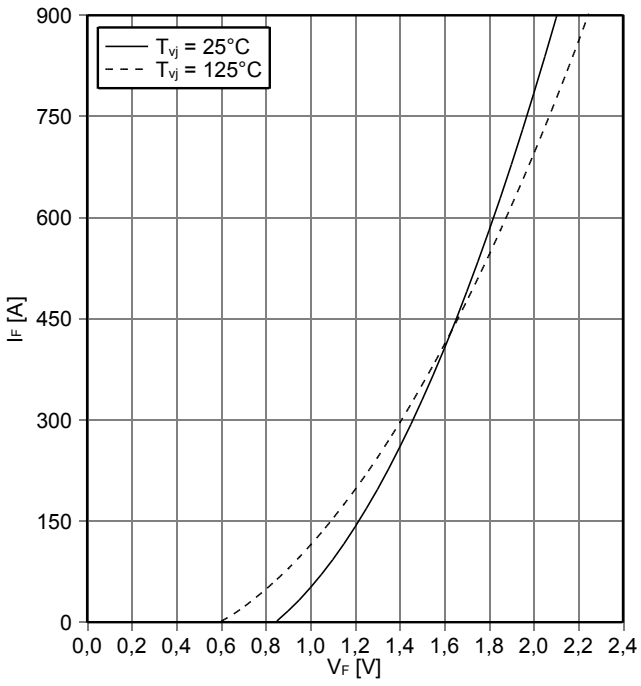
Transienter Wärmewiderstand IGBT,Wechselrichter
transient thermal impedance IGBT,Inverter
$Z_{thJC} = f(t)$



Sicherer Rückwärts-Arbeitsbereich IGBT,Wechselrichter (RBSOA)
reverse bias safe operating area IGBT,Inverter (RBSOA)
$I_C = f(V_{CE})$
V_{GE} = ±15 V, R_{Goff} = 1.6 Ω, T_{vj} = 125°C



Durchlasskennlinie der Diode, Wechselrichter (typisch)
forward characteristic of Diode, Inverter (typical)
$I_F = f(V_F)$



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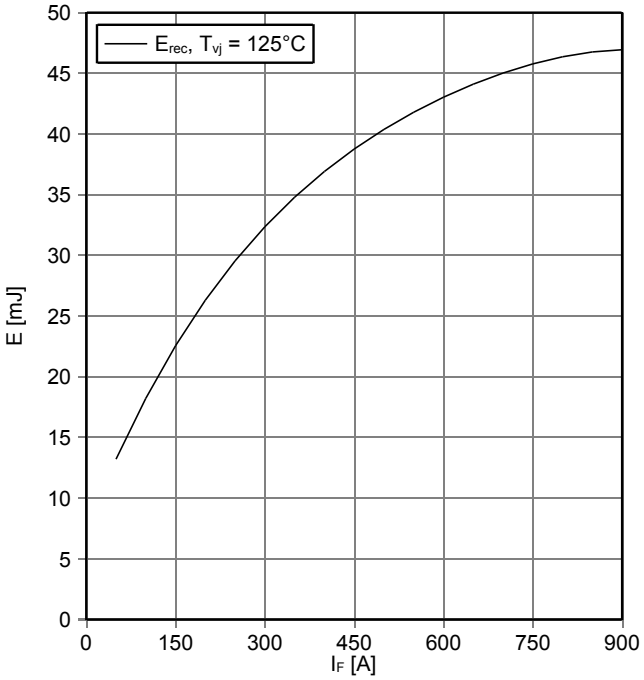
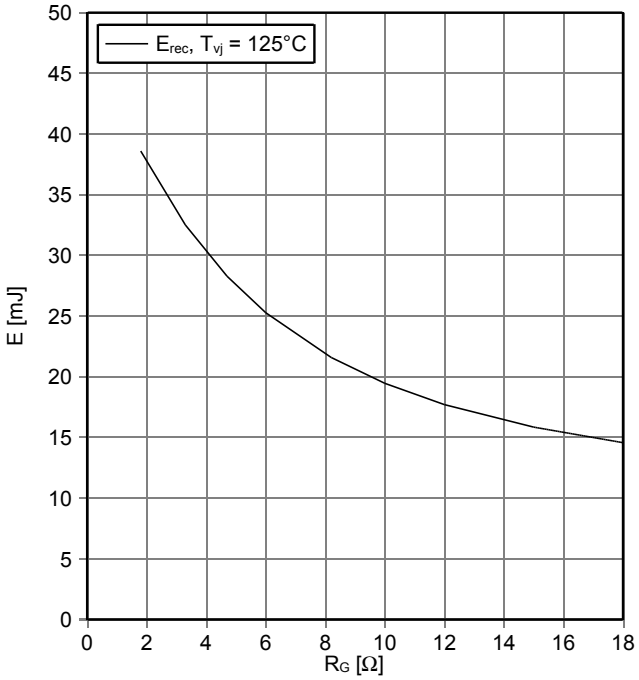
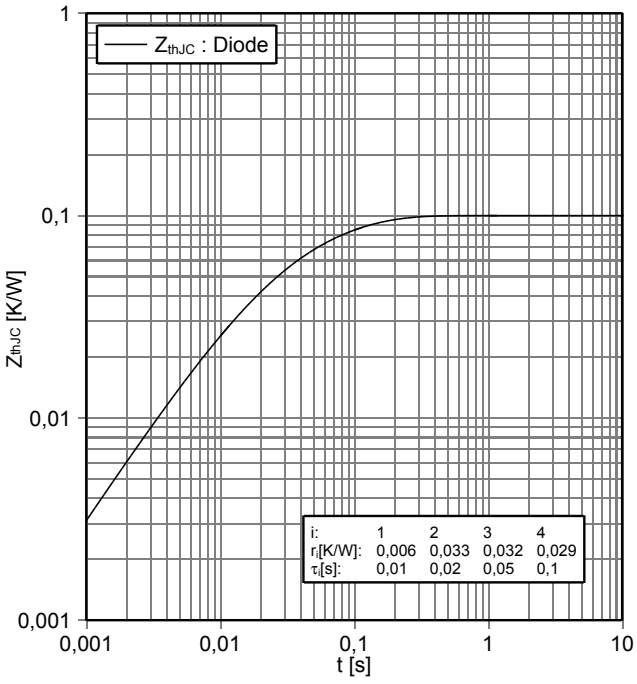
Schaltverluste Diode, Wechselrichter (typisch)
switching losses Diode, Inverter (typical)
$E_{rec} = f(I_F)$
$R_{Gon} = 1.6\ \Omega$, $V_{CE} = 600$ V



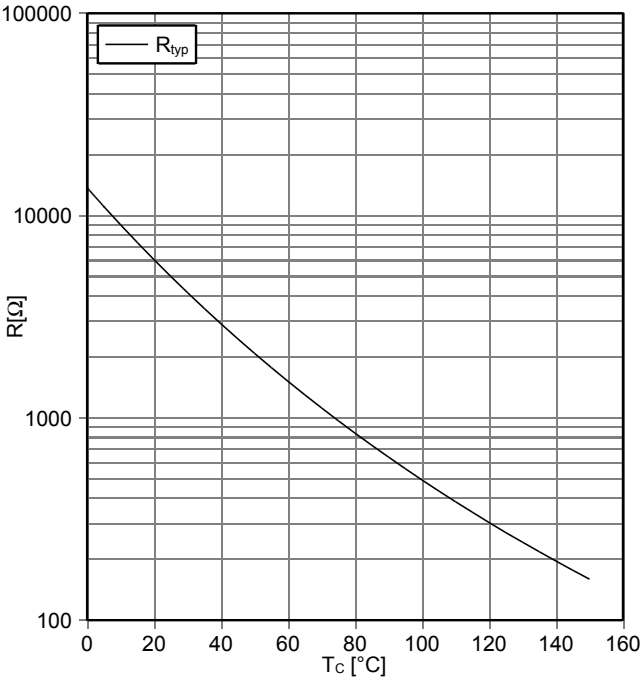
Schaltverluste Diode, Wechselrichter (typisch)
switching losses Diode, Inverter (typical)
$E_{rec} = f(R_G)$
$I_F = 450$ A, $V_{CE} = 600$ V



Transienter Wärmewiderstand Diode, Wechselrichter
transient thermal impedance Diode, Inverter
$Z_{thJC} = f(t)$



NTC-Widerstand-Temperaturkennlinie (typisch)
NTC-Thermistor-temperature characteristic (typical)
R = f (T)



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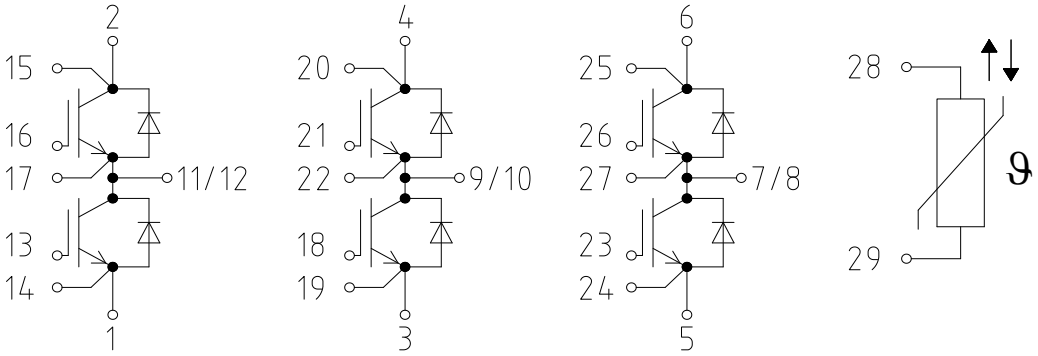
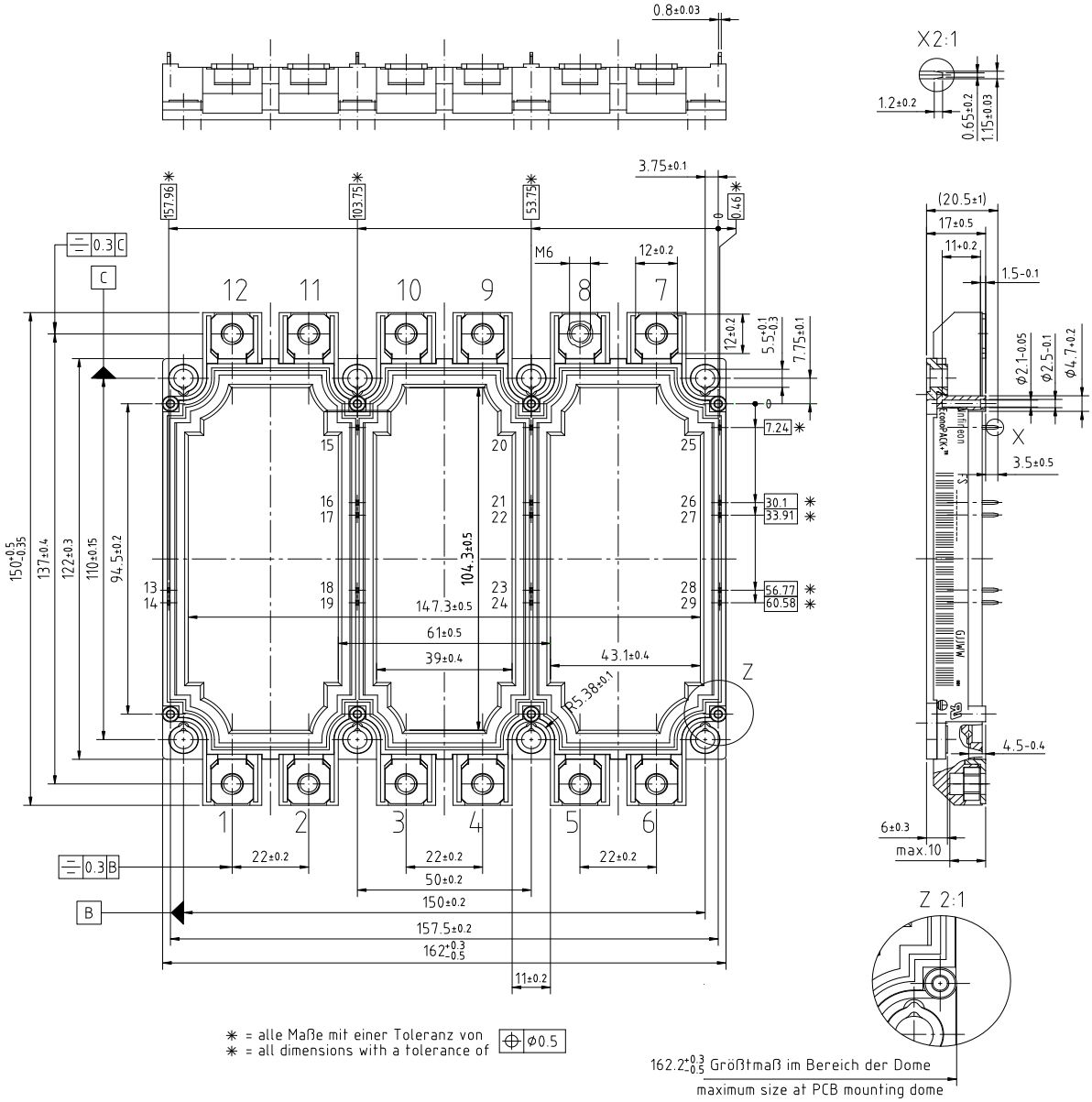
Schaltplan / circuit_diagram_headline



Gehäuseabmessungen / package outlines



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